



DONGGUAN XINGLIN ELECTRONICS CO.,LTD

SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIER

UG2KB05 THRU UG2KB100

Voltage: 50 to 1000V Current:2.0A

Features

- Glass passivated chip junction
- High case dielectric strength
- High surge current capability
- Ideal for printed circuit board

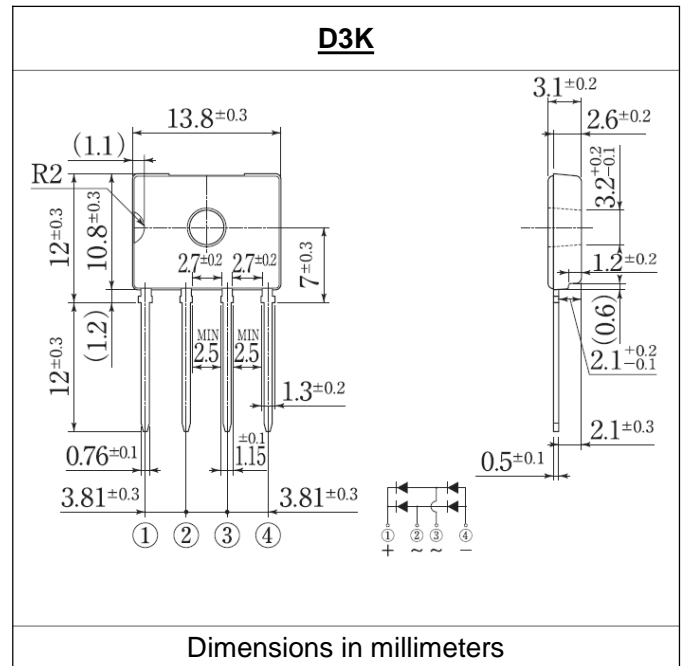
Mechanical Data

Terminal: Plated leads solderable per MIL-STD 202E, Method 208C

Case: UL-94 Class V-0 recognized Flame Retardant Epoxy

Polarity: Polarity symbol marked on body

Mounting position: any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS									
(single-phase, half -wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)									
	Symbol	UG2K B05	UG2 KB10	UG2 KB20	UG2 KB40	UG2K B60	UG2 KB80	UG2K B100	units
Maximum repetitive peak reverse voltage	V _{rrm}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V _{rms}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V _{dc}	50	100	200	400	600	800	1000	V
Maximum average forward rectified output current T _c 143°C with heatsink	I _{f(av)}	2.0							A
Peak forward surge current single sine-wave superimposed on rated load (JEDEC Method)	I _{fsm}	62							A
Maximum instantaneous forward voltage drop per leg at 1.0A	V _f	1.05							V
Rating for fusing (3ms ≤ t < 8.3ms)	I ² t	16							A ² Sec
Maximum DC reverse current at rated DC blocking voltage per leg Ta = 25°C Ta = 125°C	I _r	10.0 500							μA
Thermal resistance without heatsink with heatsink without heatsink	R _{th(ja)} R _{th(jc)} R _{th(jl)}	55 1.5 15							°C/W
Operating junction and storage temperature range	T _j , T _{stg}	-55 to +150							°C
Note:									

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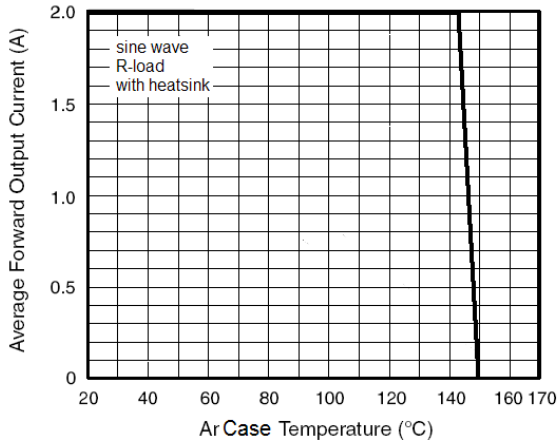


Figure 1. Derating Curve Output Rectified Current

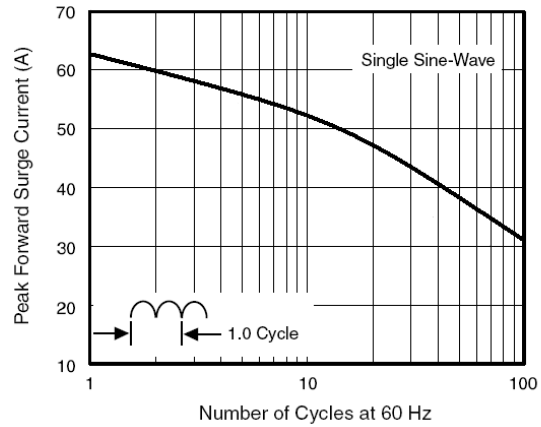


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

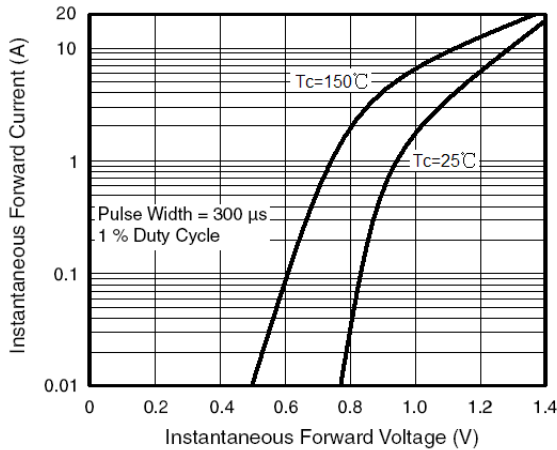


Figure 3. Typical Forward Characteristics Per Diode

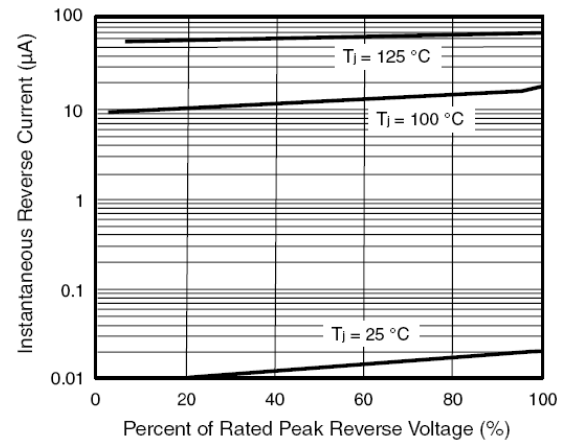


Figure 4. Typical Reverse Leakage Characteristics Per Diode

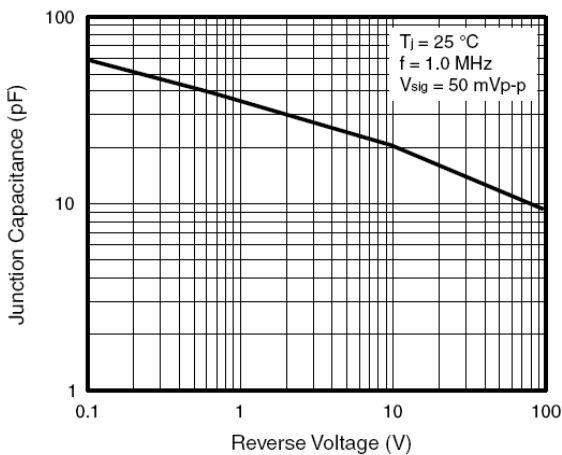


Figure 5. Typical Junction Capacitance Per Diode